

Features

- Moisture Sensitivity Level 3
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

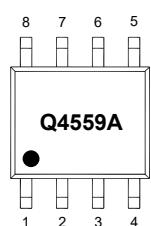
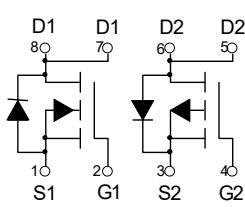
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 62.5°C/W Junction to Ambient (Note 2)

Parameter	Symbol	Rating	Unit
Total Power Dissipation (Note 4)	P _D	2.0	W
N-Channel MOSFET			
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	4.5	A
		2.8	
Pulsed Drain Current (Note 3)	I _{DM}	18	A
Single Pulsed Avalanche Energy (Note 5)	E _{AS}	24	mJ
P-Channel MOSFET			
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	-3.5	A
		-2.2	
Pulsed Drain Current (Note 3)	I _{DM}	-14	A
Single Pulsed Avalanche Energy (Note 6)	E _{AS}	24	mJ

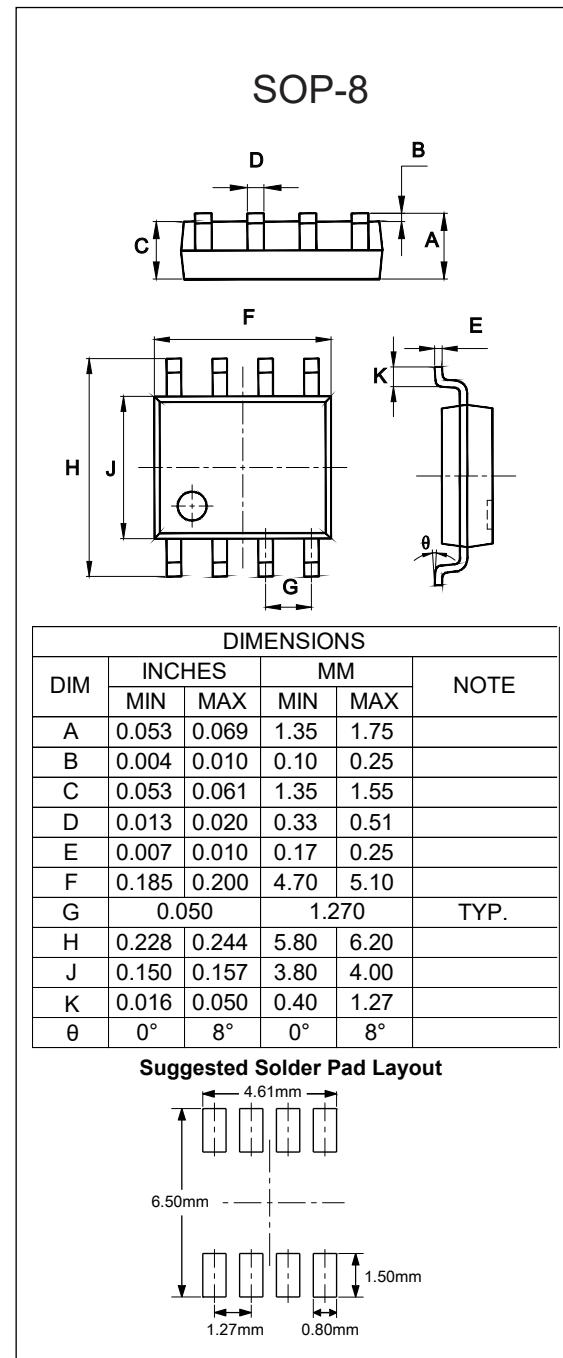
Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.
5. T_J=25°C, V_{DD}=25V, R_G=25Ω, V_G=10V, L=0.5mH.
6. T_J=25°C, V_{DD}=-25V, R_G=25Ω, V_G=-10V, L=0.5mH.

Internal Structure and Marking Code



Dual N&P-Channel MOSFET



N-Channel MOSFET Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=4.3A$		34	45	$m\Omega$
		$V_{GS}=4.5V, I_D=3.9A$		40	50	
Gate Resistance	R_g	f=1MHz, Open drain		2		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				4.5	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.7A$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F=10A, dI/dt=100A/\mu s$		22		ns
Reverse Recovery Charge	Q_{rr}			14		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		822		pF
Output Capacitance	C_{oss}			53		
Reverse Transfer Capacitance	C_{rss}			48		
Total Gate Charge	Q_g	$V_{DS}=30V, V_{GS}=10V, I_D=10A$		19.5		nC
Gate-Source Charge	Q_{gs}			3		
Gate-Drain Charge	Q_{gd}			4.8		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=30V, V_{GS}=10V, R_G=2.2\Omega, I_D=10A$		6.7		ns
Turn-On Rise Time	t_r			31		
Turn-Off Delay Time	$t_{d(off)}$			21.7		
Turn-Off Fall Time	t_f			2.6		

P-Channel Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-60			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 10V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.8	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-3.1A$		65	80	$m\Omega$
		$V_{GS}=-4.5V, I_D=-3.1A$		90	115	
Gate Resistance	R_g	f=1MHz, Open drain		3		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-3.5	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-2A$			-1.2	V
Reverse Recovery Time	t_{rr}	$I_S=-6A, di/dt=100A/\mu s$		18.6		ns
Reverse Recovery Charge	Q_{rr}			14		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$		2992		pF
Output Capacitance	C_{oss}			330		
Reverse Transfer Capacitance	C_{rss}			272		
Total Gate Charge	Q_g	$V_{DS}=-30V, V_{GS}=-4.5V, I_D=-3.1A$		4.4		nC
Gate-Source Charge	Q_{gs}			1.9		
Gate-Drain Charge	Q_{gd}			1		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-30V, V_{GS}=-10V, R_G=1\Omega, I_D=-2.4A$		14		ns
Turn-On Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			15		
Turn-Off Fall Time	t_f			5.3		

N-Channel MOSFET Curve Characteristics

Fig. 1 - Typical Output Characteristics

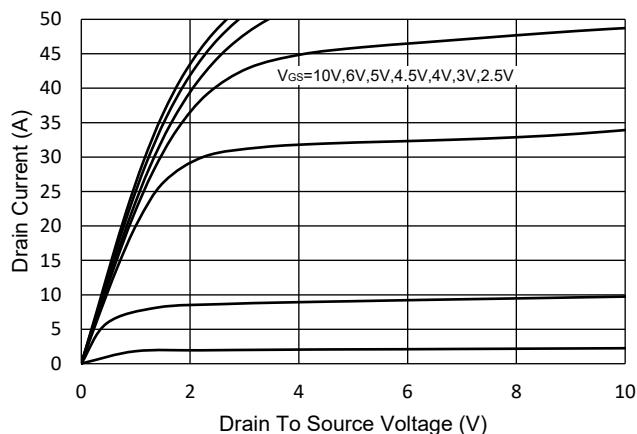


Fig.2 - Transfer Characteristic

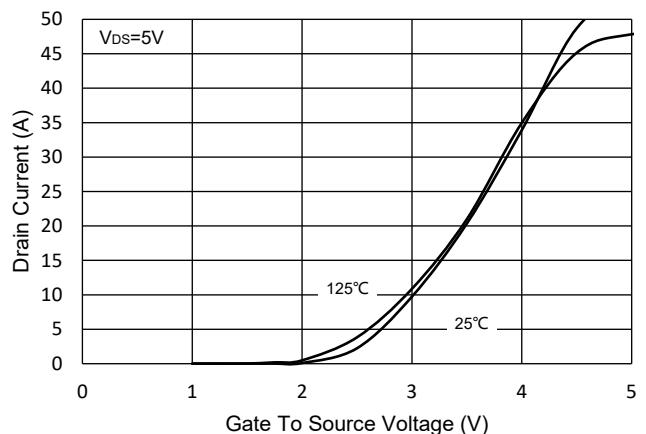


Fig.3 - $R_{DS(ON)}$ - V_{GS}

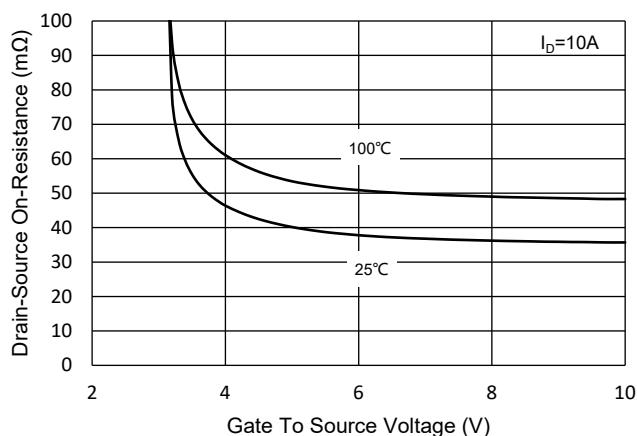


Fig.4 - $R_{DS(ON)}$ - I_D

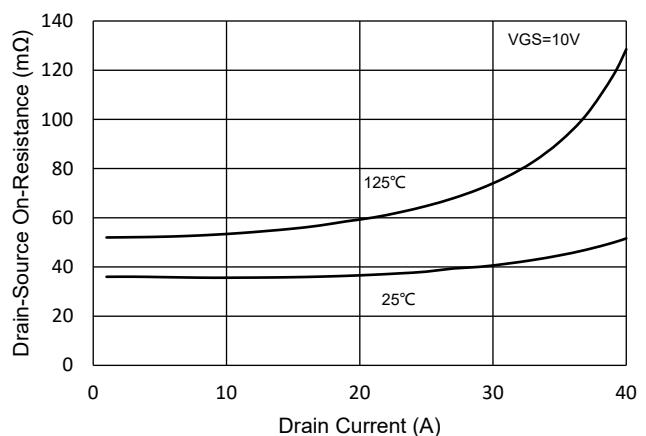


Fig.5 - Capacitance Characteristics

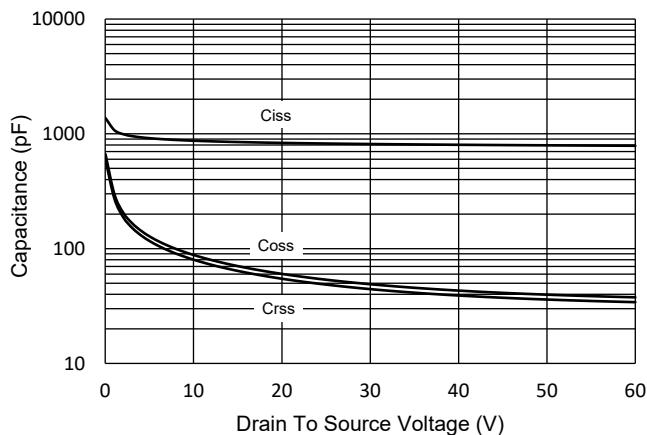
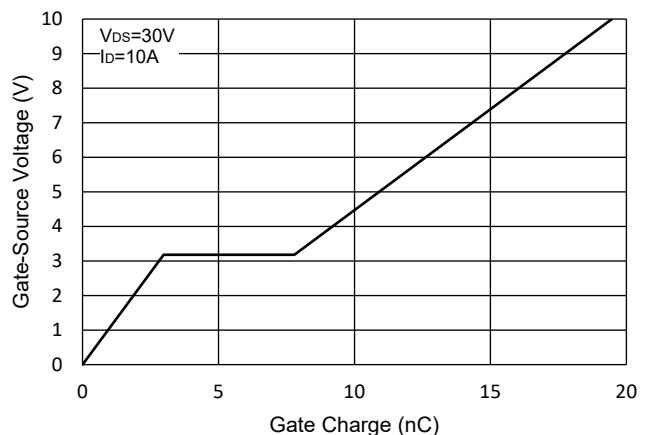


Fig.6 - Gate Charge



N-Channel MOSFET Curve Characteristics

Fig.7 - Normalized Threshold Voltage

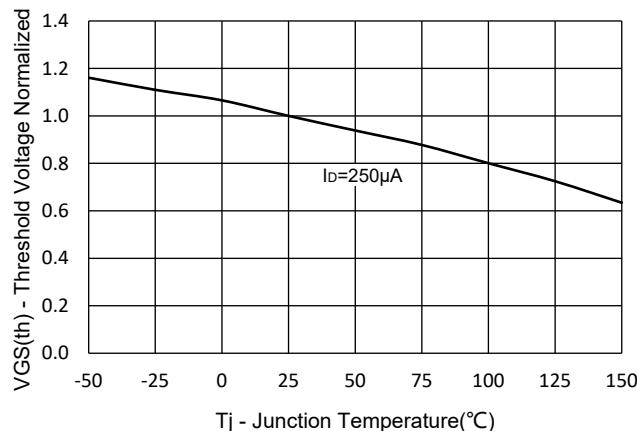


Fig.8 - Normalized On Resistance Characteristics

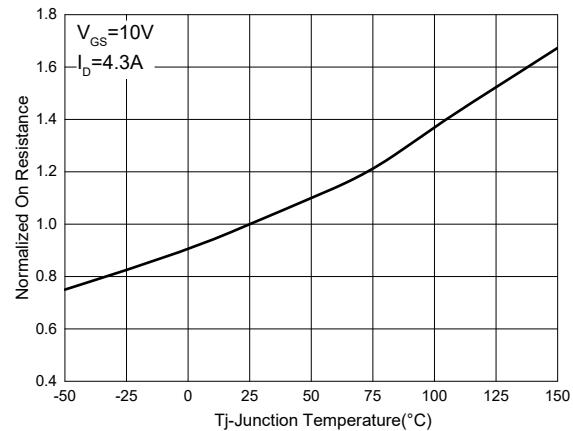


Fig.9 - I_S - V_{SD}

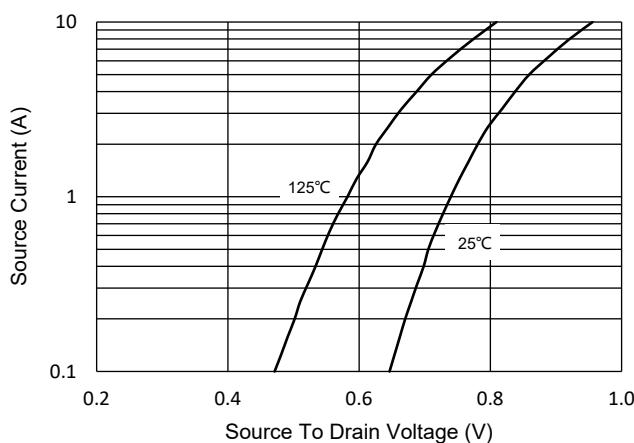


Fig.10 - Drain Current

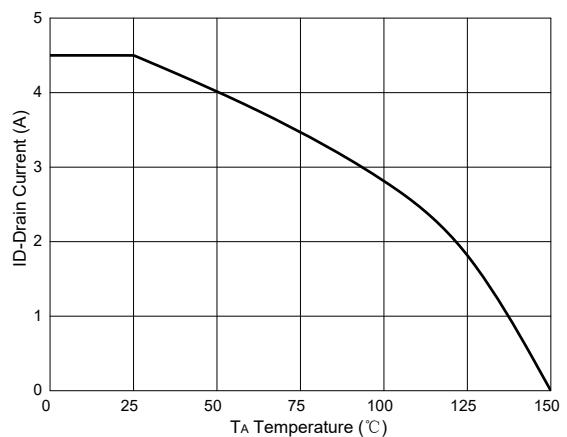
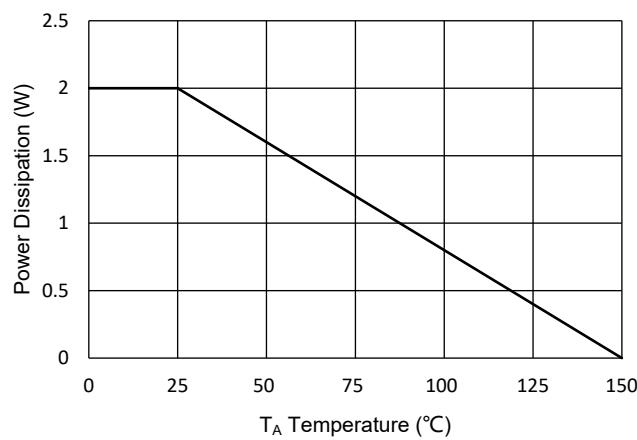


Fig.11 - PD Dissipation



N-Channel MOSFET Curve Characteristics

Fig.12 - Safe Operation Area

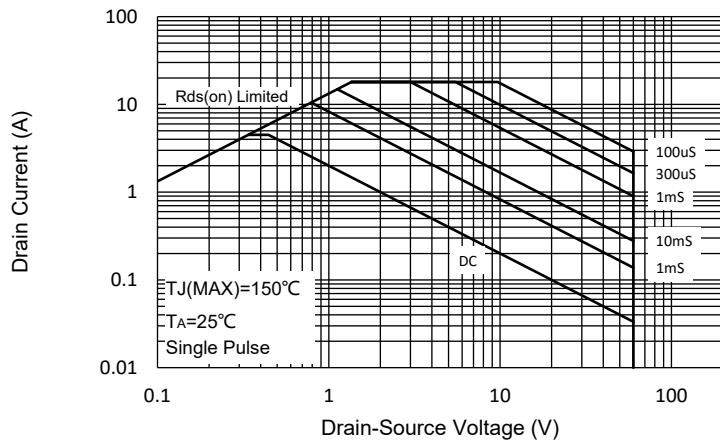
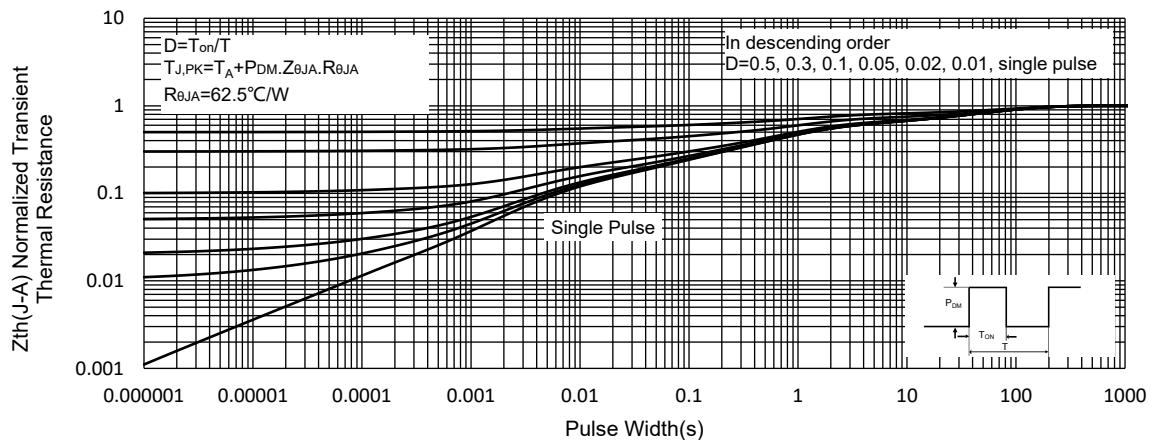


Fig.13 - Normalized Transient Thermal Impedance



P-Channel MOSFET Curve Characteristics

Fig. 1 - Typical Output Characteristics

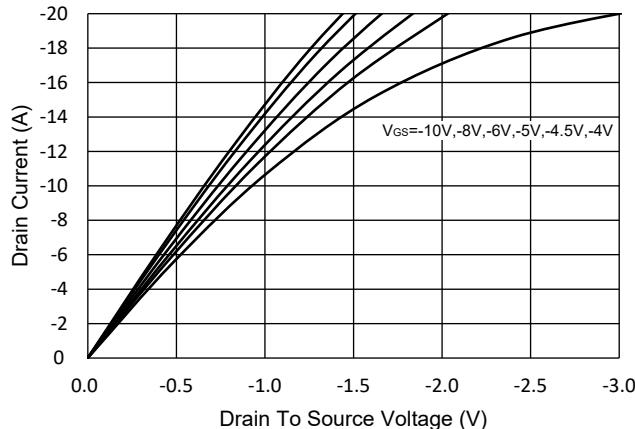


Fig.2 - Transfer Characteristic

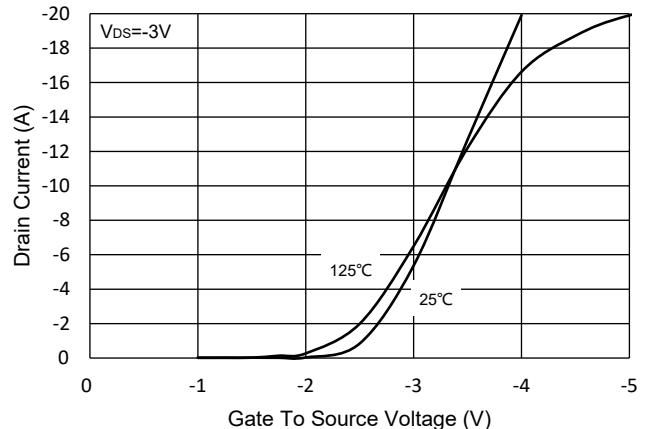


Fig.3 - $R_{DS(ON)}$ - V_{GS}

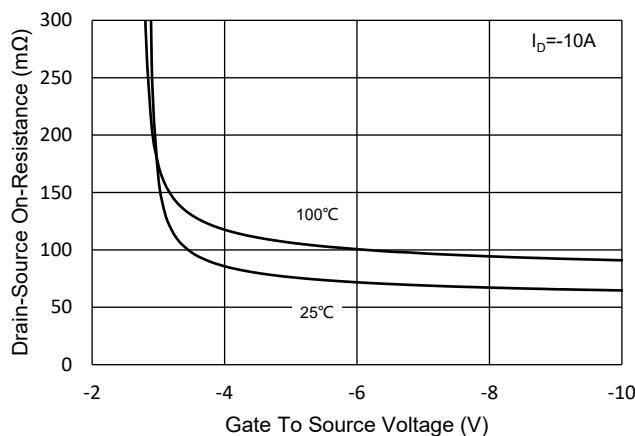


Fig.4 - $R_{DS(ON)}$ - I_D

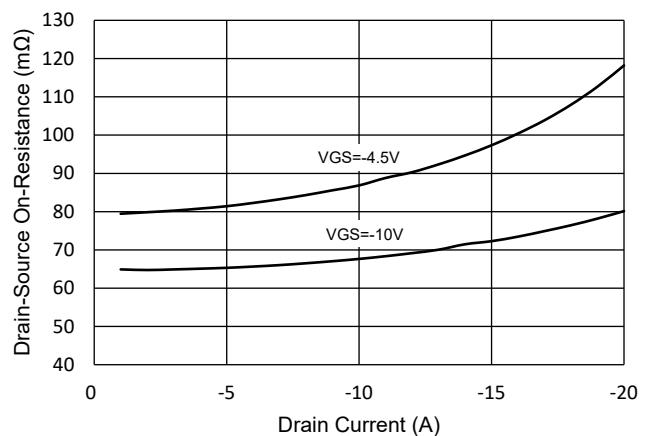


Fig.5 - Capacitance Characteristics

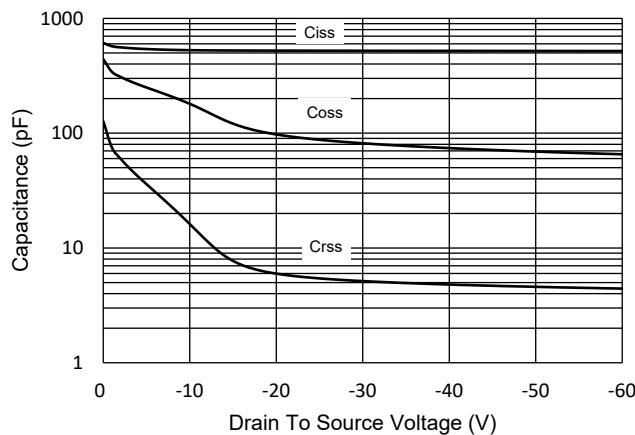
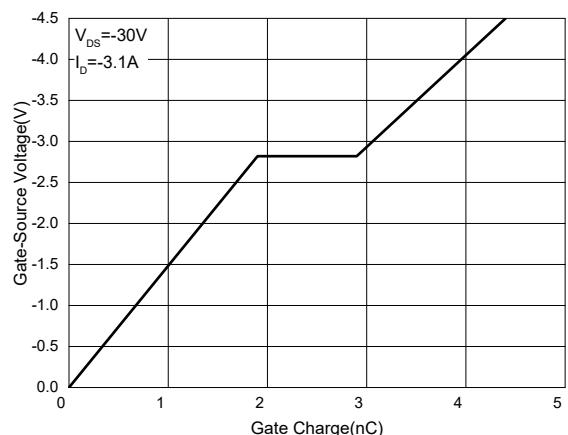


Fig. 6 - Gate Charge



P-Channel MOSFET Curve Characteristics

Fig.7 - Normalized Threshold Voltage

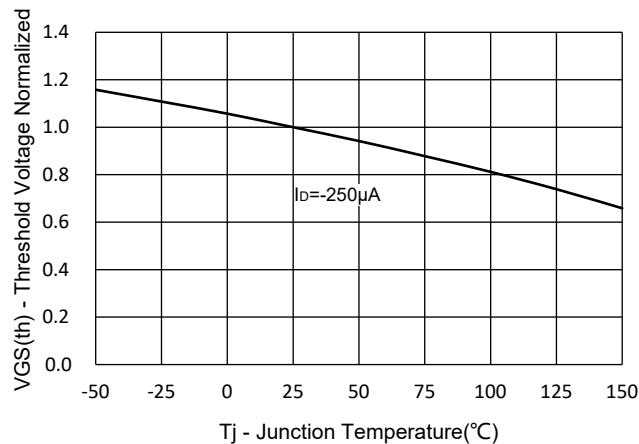


Fig.8 - Normalized On Resistance Characteristics

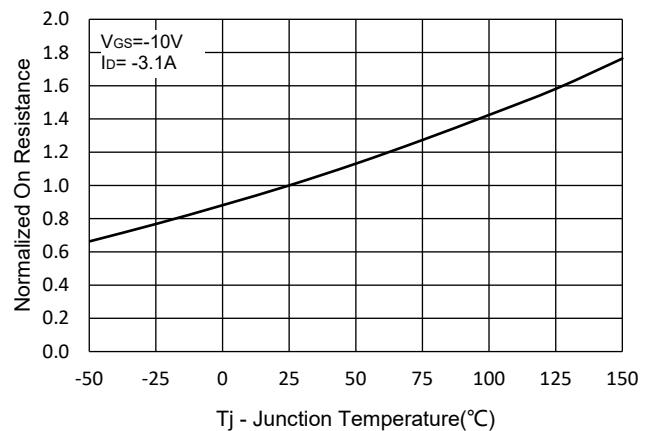


Fig.9 - I_S - V_{SD}

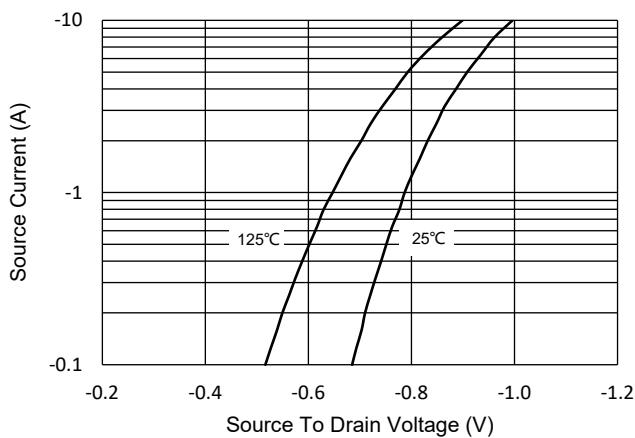


Fig.10 - Drain Current

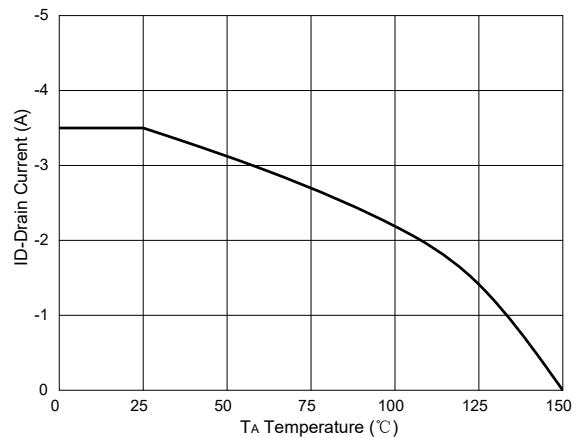
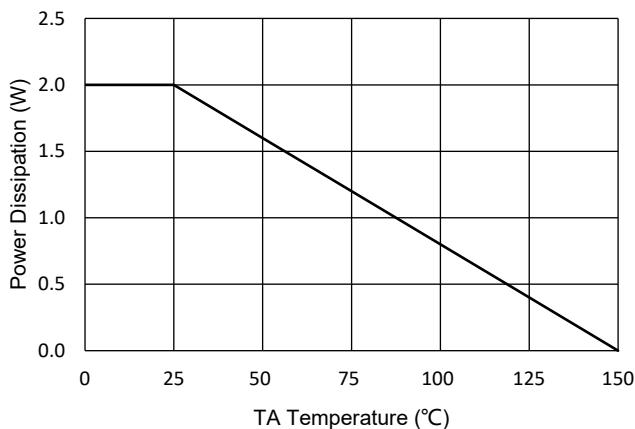


Fig.11 - PD Dissipation



P-Channel MOSFET Curve Characteristics

Fig.12 - Safe Operation Area

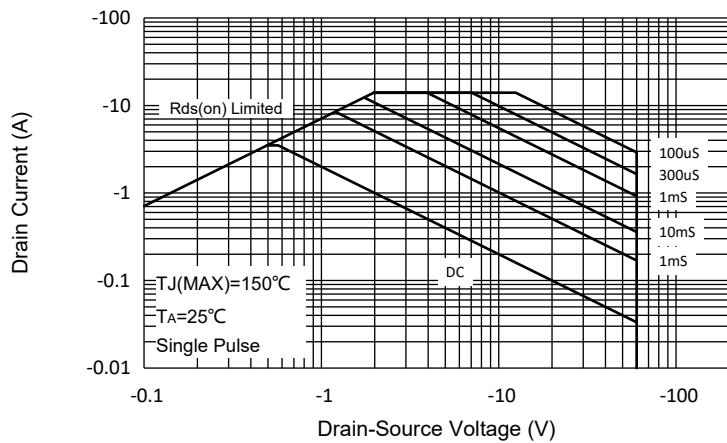
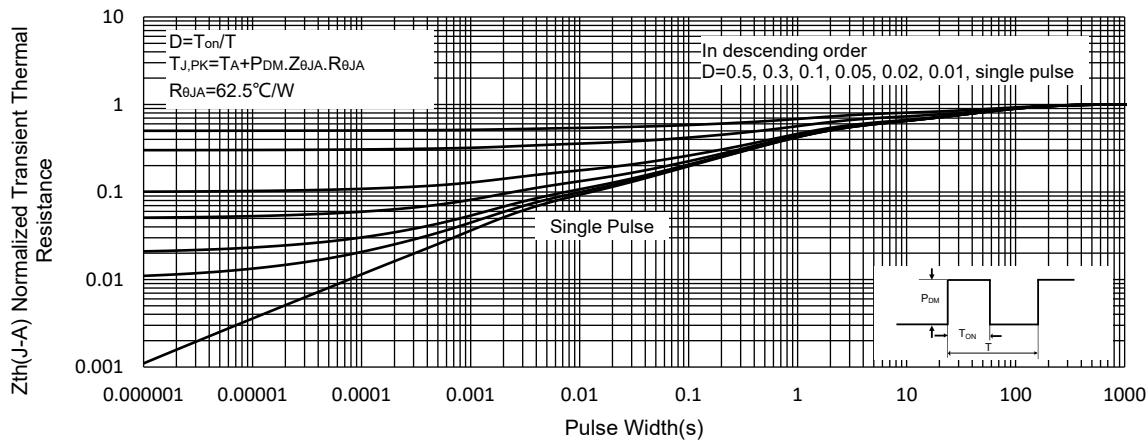


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 4Kpcs/Reel

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